



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

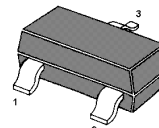
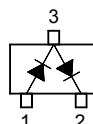
FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

BAV99

Silicon Epitaxial Planar Switching Diode

Fast switching in thick and thin-film circuits diode



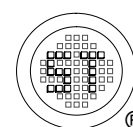
Marking Code: A7
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	85	V
Continuous Reverse Voltage	V _R	75	V
Continuous Forward Current (Double Diode Loaded)	I _F	125	mA
Continuous Forward Current (Single Diode Loaded)	I _F	215	mA
Repetitive Peak Forward Current	I _{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I _{FSM}	at t = 1 s	0.5
		at t = 1 ms	1
		at t = 1 μs	4.5
Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 1 mA at I _F = 10 mA at I _F = 50 mA at I _F = 150 mA	V _F	0.715 0.855 1 1.25	V
Reverse Current at V _R = 25 V at V _R = 75 V at V _R = 25 V, T _j = 150 °C at V _R = 75 V, T _j = 150 °C	I _R	30 1 30 50	nA μA μA μA
Diode Capacitance at V _R = 0, f = 1 MHz	C _d	1.5	pF
Reverse Recovery Time at I _F = I _R = 10 mA, I _R = 1 mA, R _L = 100 Ω	t _{rr}	4	ns



Dated : 15/06/2009



FUKUCOM COMPANY LTD.

福靈有限公司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

BAV99

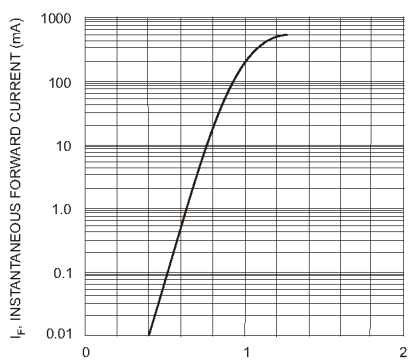


Fig. 1 Forward Characteristics

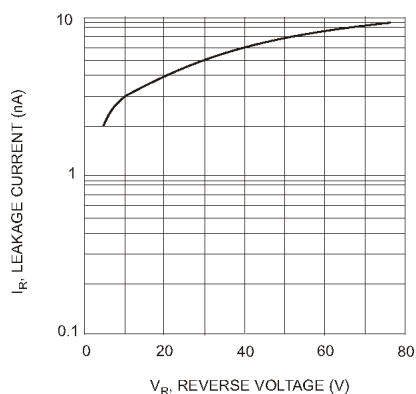


Fig. 2 Typical Leakage Current vs Reverse Voltage

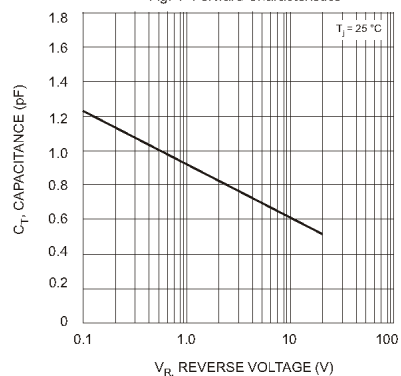
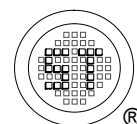


Fig. 3 Typical Total Capacitance vs Reverse Voltage



Dated : 15/06/2009